

## POWER SCHOTTKY RECTIFIERS

### MAIN PRODUCTS CHARACTERISTICS

$I_{F(av)}$	2 x 17.5 A
$V_{RRM}$	45 V
$T_j(max)$	175 °C
$V_F(max)$	0.60 V

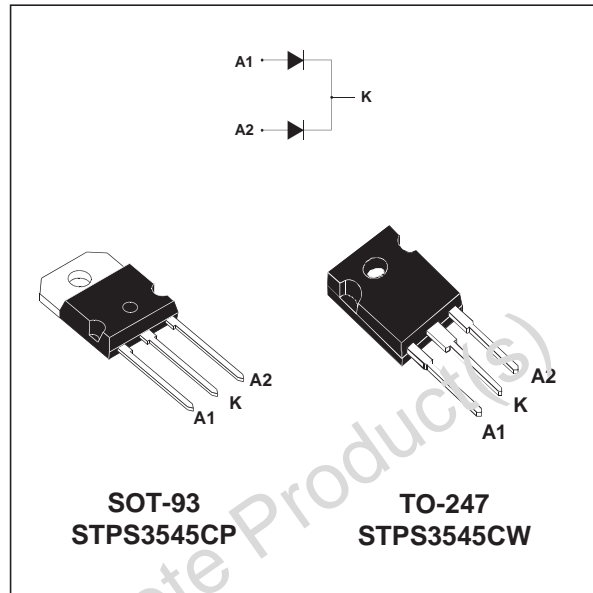
### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual center tap Schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged either in SOT-93 or TO-247 this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	45	V
$I_{F(RMS)}$	RMS forward current	30	A
$I_{F(AV)}$	Average forward current	$T_c = 150^\circ\text{C}$ $\delta = 0.5$	Per diode Per device
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10$ ms sinusoidal	220 A
$I_{RRM}$	Repetitive Peak reverse current	$t_p = 2$ $\mu\text{s}$ square $F = 1$ kHz	1 A
$I_{RSM}$	Non repetitive peak reverse current	$t_p = 100$ $\mu\text{s}$ square	3 A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1$ $\mu\text{s}$ $T_j = 25^\circ\text{C}$	6000 W
$T_{stg}$	Storage temperature range	- 65 to + 175	°C
$T_j$	Maximum operating junction temperature *	175	°C
$dV/dt$	Critical rate of rise of reverse voltage	10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	1.5	°C/W
		total	0.8	
R <sub>th(c)</sub>		Coupling	0.1	

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_J(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)} + P(\text{diode } 2) \times R_{th(c)}$

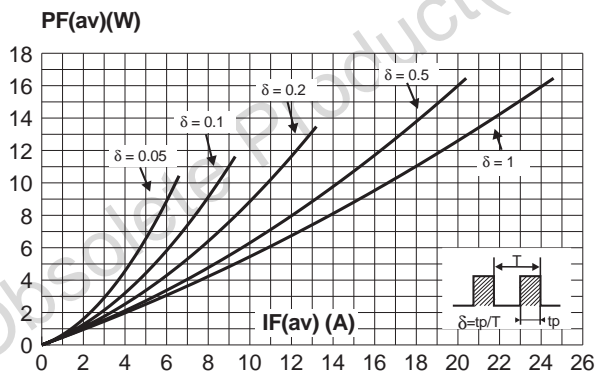
**STATIC ELECTRICAL CHARACTERISTICS (per diode)**

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			200	μA
		T <sub>j</sub> = 125°C			11	40	mA
V <sub>F</sub> *	Forward voltage drop	T <sub>j</sub> = 125°C	I <sub>F</sub> = 17.5 A		0.53	0.60	V
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 35 A			0.88	
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 35 A		0.69	0.76	

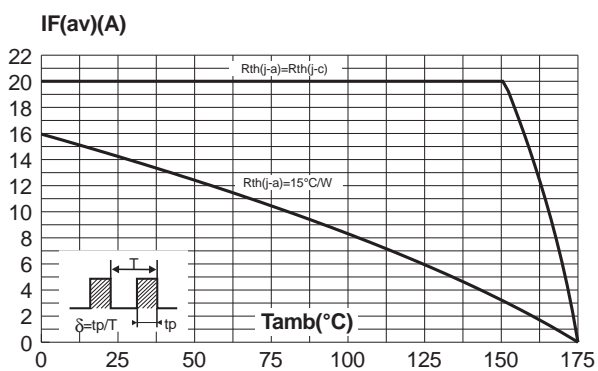
Pulse test : \* tp = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation :  
 $P = 0.44 \times I_{F(AV)} + 0.0091 I_{F(RMS)}^2$

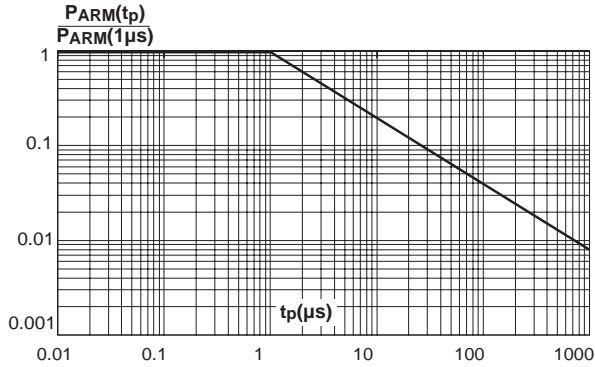
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



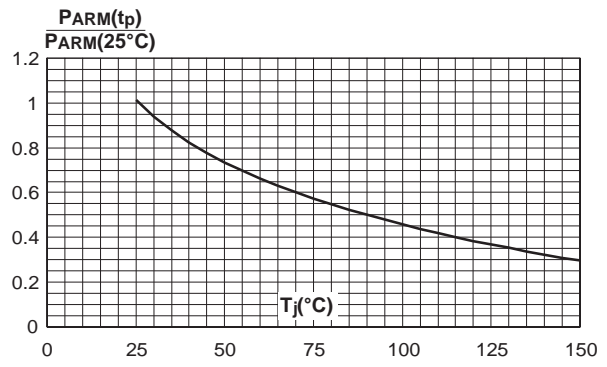
**Fig. 2:** Average current versus ambient temperature (per diode).



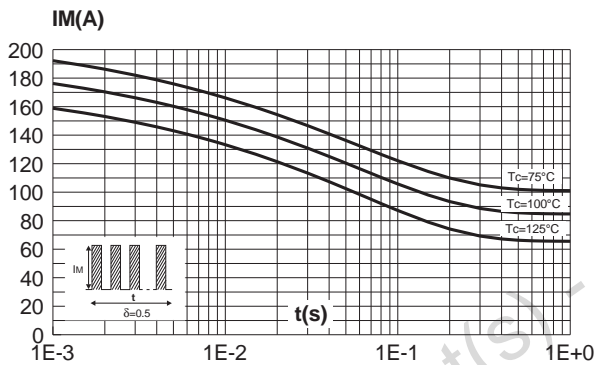
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



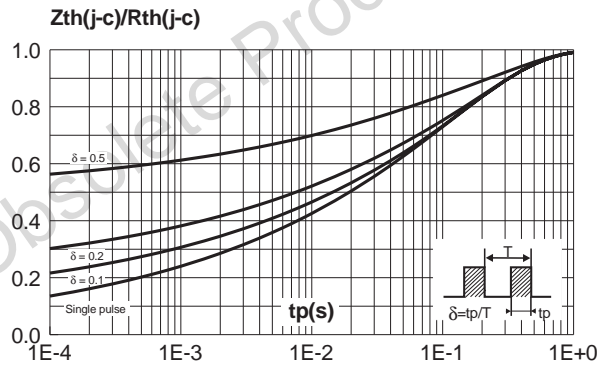
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



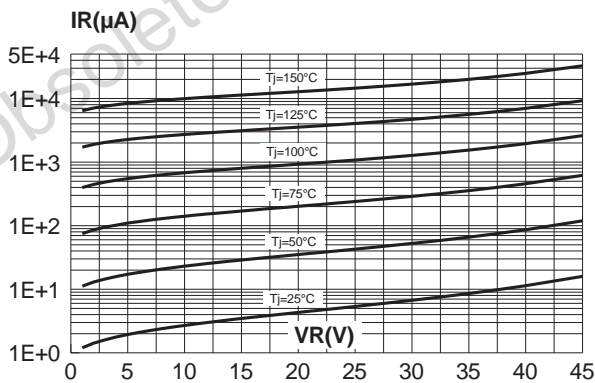
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).



**Fig. 6:** Relative variation of thermal transient impedance junction to case versus pulse duration.



**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values) (per diode).



**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values) (per diode).

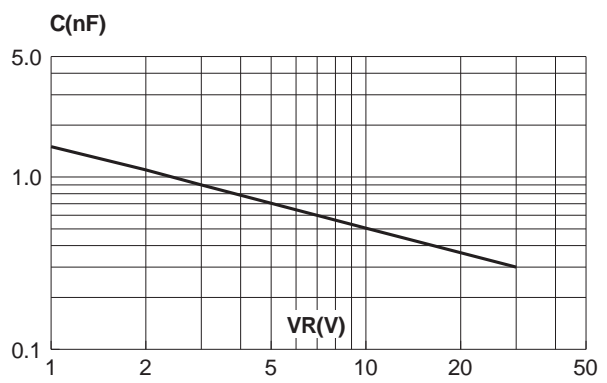
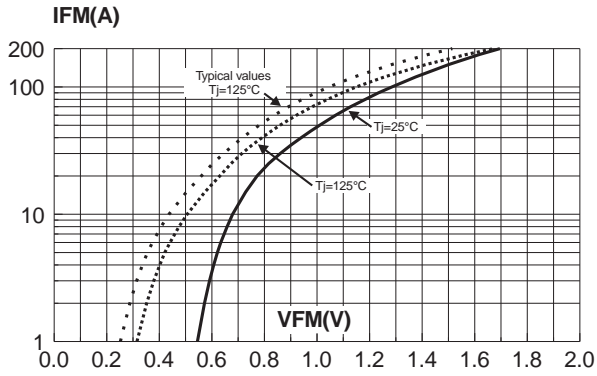
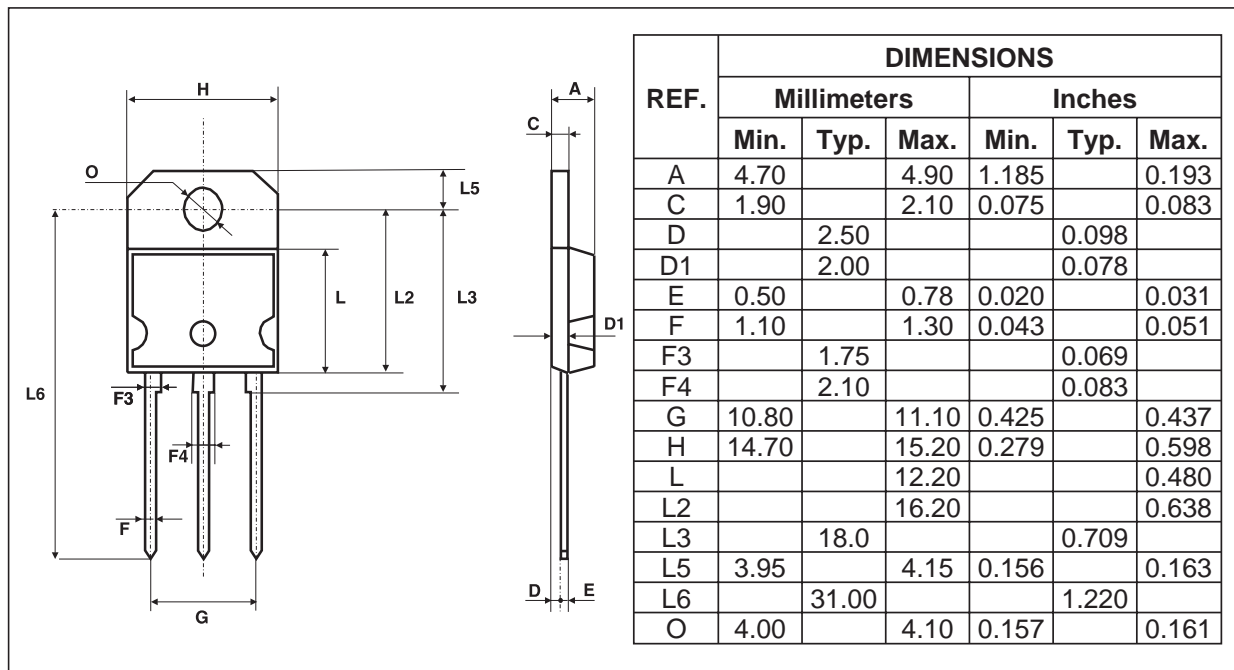


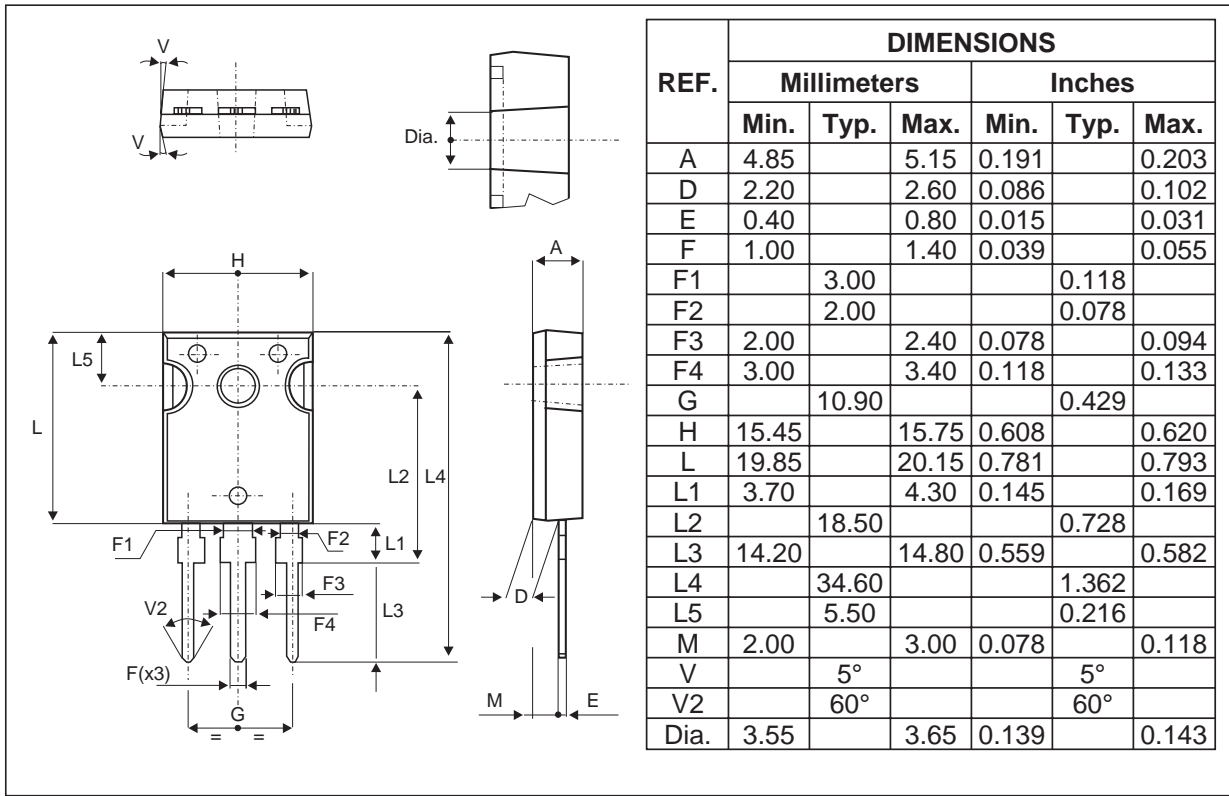
Fig. 9: Forward voltage drop versus forward current (maximum values) (per diode).



PACKAGE MECHANICAL DATA  
SOT-93



**PACKAGE MECHANICAL DATA**  
TO-247



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS3545CP	STPS3545CP	SOT-93	3.97 g.	30	Tube
STPS3545CW	STPS3545CW	TO-247	4.46 g.	30	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 0.8 N.m
- Maximum torque value: 1.0 N.m.
- Epoxy meets UL94,V0

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